



2811

PATENT

UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: VON AMMON ET AL 9
SERIAL NO: 09/813,240 EXAMINER:
FILED: MARCH 20, 2001 GROUP: 2811
TITLE: SEMICONDUCTOR WAFER MADE FROM SILICON AND METHOD
FOR PRODUCING THE SEMICONDUCTOR WAFERS

Stinson
JH
8-13-01

SUBMISSION OF INFORMATION DISCLOSURE STATEMENTS
OF DR. WOLFGANG STAUDACHER

ATT: BOX NON FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Applicants wish to bring to the attention of the Patent Examiner the two attached Information Disclosure Statements, both duly signed by Dr. Wolfgang Staudacher, and the ten (10) references listed on the first enclosed Form PTO-1449 and attached thereto and the twelve (12) references listed on the second enclosed Form PTO-1449 and attached thereto.

The relevance of the references in the first Information Disclosure Statement, is that the references are cited in the present patent application and in the Office Action of the German Patent and Trademark Office and may be material to the examination of the application.

The relevance of the references in the Supplemental Information Disclosure Statement, is that the reference are cited

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in the European Search Report and may be material to the examination of the application.

Since this Information Disclosure Statement and Supplemental Information Disclosure Statement are being filed prior to a first Office Action, it is believed that no fee is due. However, if it is determined that a fee is due, the Commissioner is hereby authorized to charge, or to credit any over payment, to our Deposit Account Number 03-2468.

It is respectfully requested that the Information Disclosure Statement and the Supplemental Information Disclosure Statement be considered and placed into the application file.

Respectfully submitted,

WILFRIED VON AMMON ET AL 9



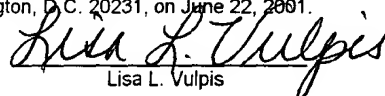
Allison C. Collard, Reg. No. 22,532
Edward R. Freedman, Reg. No. 26,048
Attorneys for Applicants

COLLARD & ROE, P.C.
1077 Northern Boulevard
Roslyn, New York 11576
(516) 365-9802

Encl.:

- 1) Information Disclosure Statement Of Dr. Wolfgang Staudacher
- 2) PTO-form 1449 w/copies of 10 references
- 3) Copy of the Office Action of the German Patent Office
- 4) Supplemental Information Disclosure Statement Of Dr. Wolfgang Staudacher
- 5) PTO-form 1449 w/copies of 12 references
- 6) Copy of the European Search Report

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: ASSISTANT COMMISSIONER OF PATENTS, Washington, D.C. 20231, on June 22, 2001.


Lisa L. Vulpis

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

VON AMMON ET AL

Serial Number: 09/813,240

Group Art Unit: 2811

Filed: March 20, 2001

For: SEMICONDUCTOR WAFER MADE FROM SILICON AND METHOD FOR
PRODUCING THE SEMICONDUCTOR WAFER



Information Disclosure Statement

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir or Madam:

I, Wolfgang Staudacher, associated with the preparation and prosecution of the above-identified application, residing at Seebauerstraße 4, 81735 München, Germany, wish to call the attention of the Patent Examiner to the references enumerated on the enclosed PTO Form-1449.

I believe the documents enumerated on the enclosed Form PTO-1449 and attached thereto, are cited in the European Search Report and may be material to the examination of the application.

Therefore, it is respectfully requested that the foregoing Information Disclosure Statement be considered by the Examiner and incorporated into the file of this application.

I wish to comment as follows concerning the prior art references enumerated on PTO Form-1449:

Patent Abstract of Japan corresponding to JP 11 189495 is already in English language.

Patent Abstract of Japan corresponding to JP 07 126 094 is already in English language.

Patent Abstract of Japan corresponding to JP 61 178 495 is already in English language.

Iino E. et al.: "Cavities Owing to Hydrogen in Si Single Crystals Grown by Continuously Charging CZ Method", Materials Science and Engineering, Vol. B36, 1996, p. 146-149 is already in English language.

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Hara A. et al.: "Influence of Grown-in Hydrogen on Thermal Donor Formation and Oxygen Precipitation in Czochralski Silicon Crystals", Japanese Journal of Applied Physics, Vol. 33, No. 10, Part 1, 1994, p. 5577-5584 is already in English language.

Hara A. et al.: "Hydrogen in As-Grown Czochralski Silicon Crystals", Extended Abstracts of the International Conference on Solid State Devices and Materials, Japan Society of Applied Physics, 1993, p. 1014-1016 is already in English language.

For DE 2 147 514 the corresponding GB 1 365 724 is enclosed.

EP 0 170 788 is already in English language.

US 5,505,157 is already in English language.

For EP 0 829 559 the corresponding US 5,935,320 is enclosed.

Signed this 14th day of May, 2001.


.....
Dr. Wolfgang Staudacher

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

VON AMMON ET AL

Serial Number: 09/813,240

Group Art Unit: 2811

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For EP 0 725 169 an English Derwent Abstract is enclosed.

E. Iino et al., Materials Science and Engineering B 36 (1996) 146-149 is already in English language.

For DE 35 45 383 an English Derwent Abstract is enclosed.

For WO 99/57344 an English Derwent Abstract is enclosed.

US 4,210,486 is already in English language.

US 5,641,353 is already in English language.

US 3,660,062 is already in English language.

Signed this 11th day of April, 2001.


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Dr. Wolfgang Staudacher